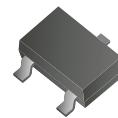


SMD Switching Diode

Comchip
SMD Diode Specialist

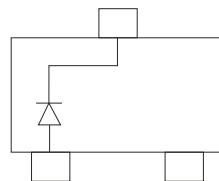
CDST116-G RoHS Device



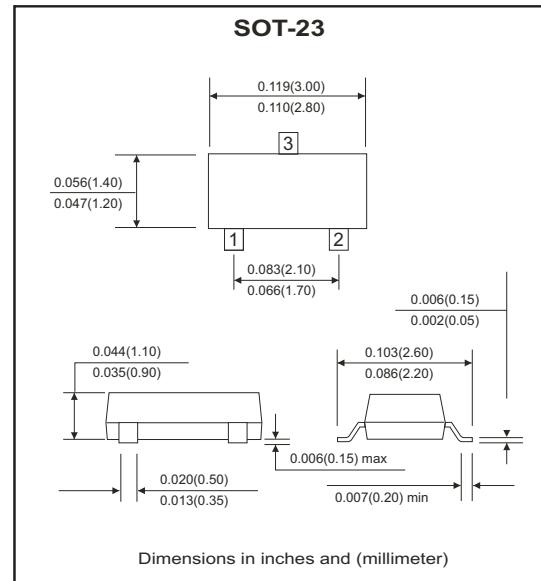
Features

- Low leakage current applications.
- Medium speed switching times.

Polarity:



Marking: JV



Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak repetitive peak reverse voltage	V _{R_{RM}}		
Working peak reverse voltage	V _{R_{WM}}	75	V
DC blocking voltage	V _R		
Forward continuous current	I _{FM}	215	mA
Power dissipation	P _D	250	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{STG}	-55 to +150	°C

Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ.	Max	Unit
Reverse breakdown voltage	I _R =100μA	V _{(BR)R}	75			V
Forward voltage	I _F =1mA	V _{F1}			0.9	V
	I _F =10mA	V _{F2}			1	V
	I _F =50mA	V _{F3}			1.1	V
	I _F =150mA	V _{F4}			1.25	V
Reverse current	V _R =75V	I _R			5	μA
Capacitance between terminals	V _R =0V, f=1MHz	C _T		2		pF
Reverse recovery time	I _F =I _R =10mA, I _{RR} =0.1×I _R , RL=100Ω	t _{rr}			3	nS

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RATING AND CHARACTERISTIC CURVES (CDST116-G)

Fig.1 - Forward Current Derating Curve

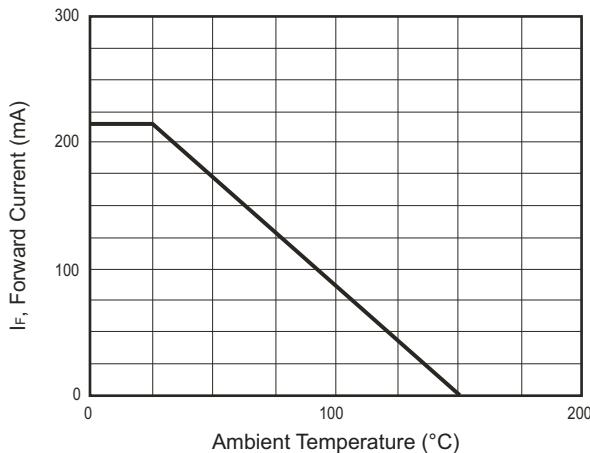


Fig.2 - Forward Voltage Characteristics

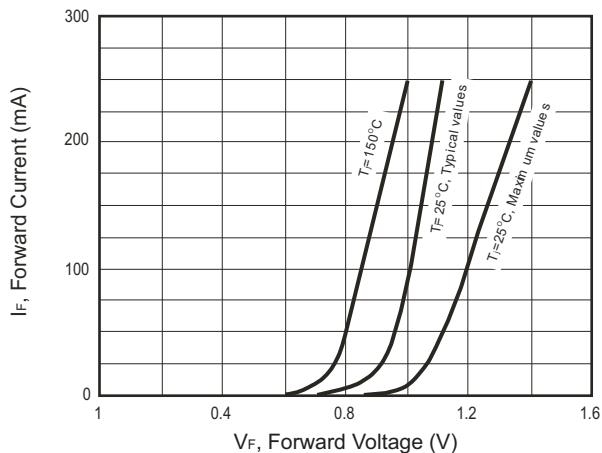


Fig.3 - Reverse Characteristics

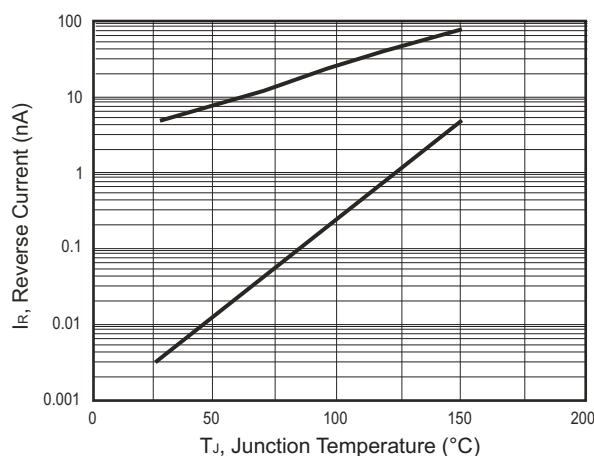


Fig.4 - Diode Capacitance Characteristics

